

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Continuous Collector Current	lc	-100	mA
Peak Collector Current	Ісм	-200	mA
Peak Emitter Current	I _{EM}	-200	mA
Peak Base Current	I _{BM}	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Rower Dissinction	(Note 6)	P	310	mW	
Power Dissipation	(Note 7)	PD P	350	11100	
Thermal Resistance, Junction to Ambient	(Note 6)	D	403	°C/W	
	(Note 7)	R _{0JA}	357	C/VV	
Thermal Resistance, Junction to Leads (Note 8)		R _{θJL}	350	°C/W	
Operating and Storage Temperature Range		T _J ,T _{STG}	-65 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

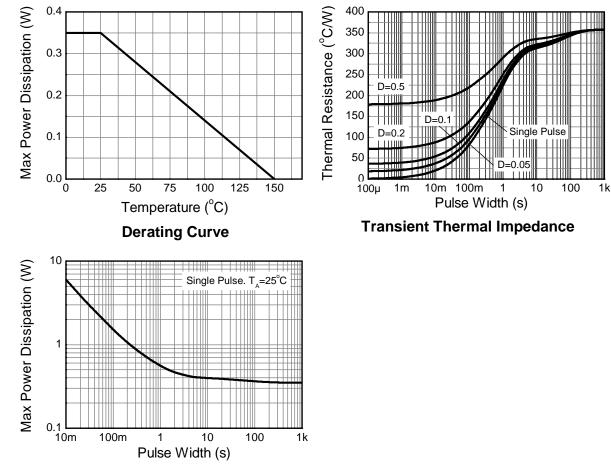
Notes: 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

7. Same as Note 6, except the device is mounted on 15mm x 15mm 1oz copper.

Barrow Comparison of the device is mounted of romma forming to any 102 control of the leads).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



Pulse Power Dissipation



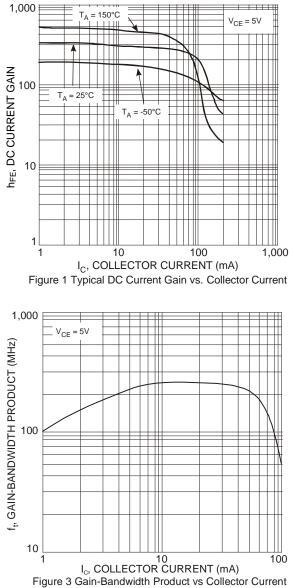
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

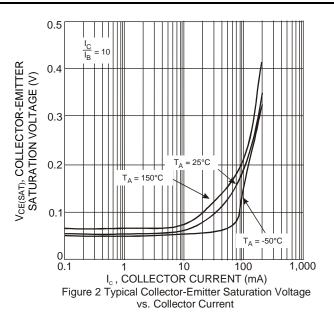
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BVCBO	-50		_	V	$I_{\rm C} = -10\mu A$
Collector-Emitter Breakdown Voltage (Note 10)		BVCEO	-45	_	_	V	$I_c = -10 \text{mA}$
Emitter-Base Breakdown Voltage		BV _{EBO}	-5	_	_	V	$I_E = -1\mu A$
Collector Cutoff Current			Ісво —		-15	nA	V _{CB} = -30V
		ICBO			-4	μA	V _{CB} = -30V, T _J = +150°C
Collector Emitter Cutoff Current		ICES	_	_	-15	nA	$V_{CE} = -50V$
Emitter-Base Cutoff Current		I _{EBO}		_	-100	nA	$V_{EB} = -5V$
Small Signal Current Gain (Note 10)	AC857BQ	h		330	_		
Sinali Signal Current Gain (Note 10)	AC857CQ	h _{fe}		600	_		
Input Impedance (Note 10)	AC857BQ	b.	_	4.5	_	kΩ	
input impedance (Note 10)	AC857CQ	h _{ie}		8.7	—	K12	$I_{C} = -2.0 \text{mA}, V_{CE} = -5 \text{V}$
Output Admittance (Note 10)	AC857BQ	h		30	_	μS	f = 1.0kHz
Output Admittance (Note 10)	AC857CQ	h _{oe}	_	60	_	μο	
Reverse Voltage Transfer Ratio (Note 10)	AC857BQ	h		2x10 ⁻⁴	—		
Reverse voltage mansfer Ratio (Note TO)	AC857CQ	h _{re}		3x10 ⁻⁴	_		
DC Current Gain (Note 10)	AC857BQ	b	220	290	475	—	$I_{C} = -2.0 \text{mA}, V_{CE} = -5 \text{V}$
	AC857CQ	h _{FE}	420	520	800		
Collector-Emitter Saturation Voltage (Note 10)		V _{CE(SAT)}	_	-75	-300	mV	$I_{C} = -10mA$, $I_{B} = -0.5mA$
		VCE(SAT)		-250	-650	IIIV	$I_{C} = -100 \text{mA}, I_{B} = -5.0 \text{mA}$
Base-Emitter Turn-On Voltage (Note 10)			-600	-650	-750	mV	$I_{C} = -2mA, V_{CE} = -5V$
Base-Emilier rum-On vollage (Note TO)		V _{BE(ON)}	_	_	-820		$I_{C} = -10 \text{mA}, V_{CE} = -5 \text{V}$
Base-Emitter Saturation Voltage (Note 10)		M		-700	_	mV	$I_{\rm C}$ = -10mA, $I_{\rm B}$ = -0.5mA
		V _{BE(SAT)}	_	-850	-1100	IIIV	$I_{C} = -100 \text{mA}, I_{B} = -5 \text{mA}$
Output Capacitance		C _{obo}		3	_	pF	$V_{CB} = -10V, f = 1.0MHz$
Transition Frequency		f _T	100	200	—	MHz	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$
Noise Figure		NF	_	2	10	dB	$\label{eq:VCE} \begin{array}{l} V_{CE} = \texttt{-5V}, \ I_{C} = \texttt{-200}\muA \\ R_{S} = 2k\Omega, \ f = 1kHz \\ \Deltaf = 200Hz \end{array}$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



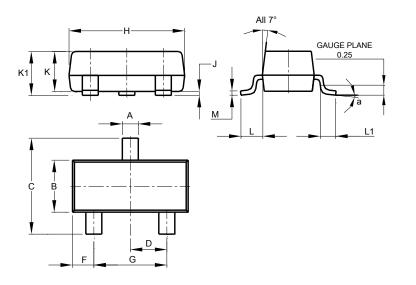




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

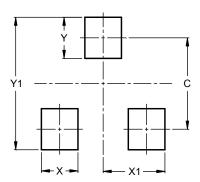
SOT23



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
с	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
H	2.80	3.00	2.90		
J	0.013	0.10	0.05		
Κ	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
Μ	0.085	0.150	0.110		
а	0°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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